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(24)

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2005 01 03

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2e

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1a 1d  
2a 2h

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 100 : 102 :  
 104 : 106 :  
 106a : 108 : 1  
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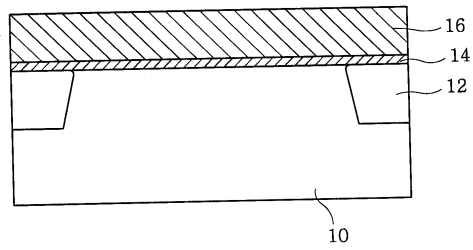
(sub-micron) 가 가  
 가 가 가 가  
 Semiconductor Field Effect Transistor) (Metal Oxide S  
 1a 1d  
 1a (active region) (10) (isolation region) (isolation process) (12) (d  
 (10) (14) (16) (16)  
 opened polysilicon) 1b (18) (16)  
 1c (18) (16)  
 1d (16a) (18) (16)  
 (16a) (14a)  
 가  
 1 1  
 1 2 1 1 가 2  
 1 2 1 1  
 1 2 1 1

2a 2h  
 , , ( )  
 2a , (100) (100) (104)  
 , (102) (doped polysilicon) ,  
 (106) (SiN) (open region) (110) (108)  
 1 (108) (110)  
 2b 1 (108) (108a) (110) (110) ( )  
 110 (110) 가 1 (108) (110)  
 1 2 (112) (SiO2) 2  
 2c (112) 1 (108) (108a) 2 (112)  
 2d 1 (108a) 2 (112) (108a) 2  
 1 (112a) (112a) 'T'  
 (chemical mechanical polishing process) (blanket etch)  
 2e 2 (112a) (108a) (overlap) 'T' (114)  
 2f (114) (106) (108a)  
 , (114) (108b) 2 (112a) (106)  
 1 (108b) 2 (112a) (106)  
 2g , 2 (112a) (108b) (106)  
 1 (108b) (106a) (106a)  
 (106) 2h , 1 (108b) (106a) (106a)  
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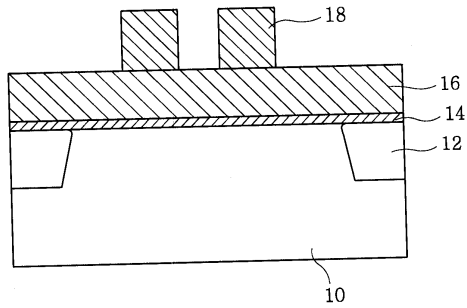
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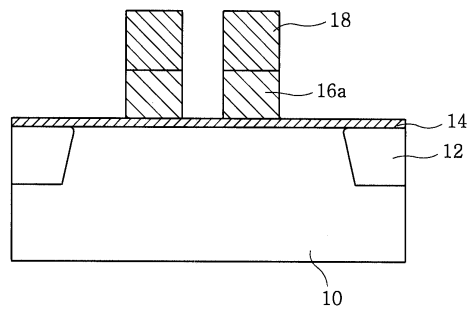
1a



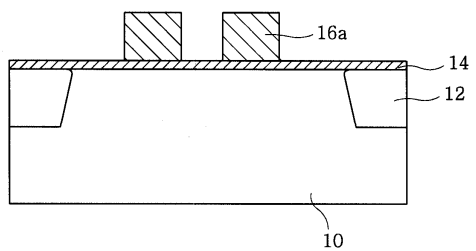
1b



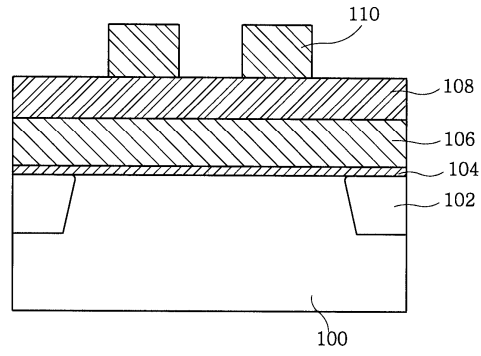
1c



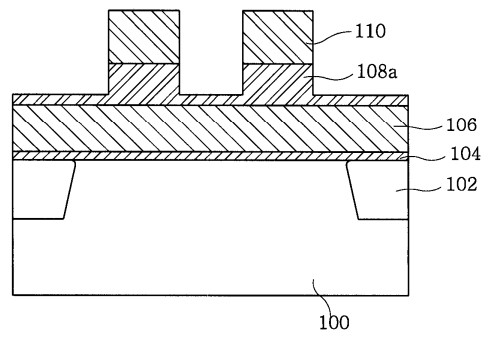
1d



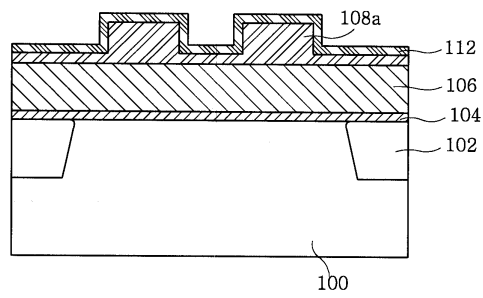
2a



2b



2c



2d

